

描述 / Descriptions

PDFN3×3A-8L 塑封封装 N 沟道 MOS 场效应管。

N-Channel Enhancement Mode Field Effect Transistor in a PDFN3×3A-8L Plastic Package.

特征 / Features

$V_{DS} (V) = 40V$

$I_D = 82A (V_{GS} = \pm 20V)$

$R_{DS(ON)} @ 10V \leq 3m\Omega (Typ. 2.5m\Omega)$

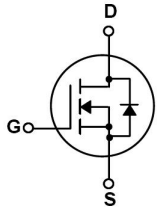
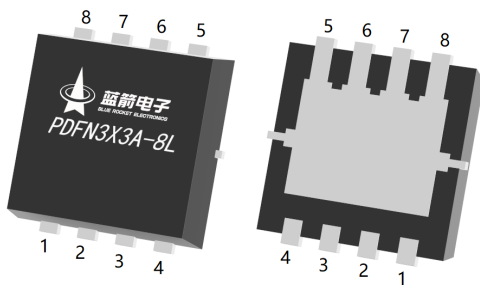
$R_{DS(ON)} @ 4.5V \leq 5m\Omega (Typ. 3.5m\Omega)$

无卤产品。HF Product.

用途 / Applications

负载开关应用、电池电源管理。

Load Switch Applications, Battery Power Management.

内部等效电路 / Equivalent Circuit**引脚排列 / Pinning**

出脚	定义
Pin1	S
Pin2	S
Pin3	S
Pin4	G
Pin5	D
Pin6	D
Pin7	D
Pin8	D

印章代码 / Marking

见印章说明。

See Marking Instructions.


极限参数 / Absolute Maximum Ratings(Ta=25°C)

参数 Parameter		符号 Symbol	数值 Rating	单位 Unit
Drain-Source Voltage		V_{DS}	40	V
Drain Current		$I_D(T_c=25^{\circ}\text{C})$	57	A
Drain Current - Pulsed		I_{DM}	137	A
Gate-Source Voltage		V_{GS}	± 20	V
Single Pulsed Avalanche Energy		E_{AS}	348	mJ
Avalanche Current		I_{AS}	33	A
Power Dissipation		$P_D(T_c=25^{\circ}\text{C})$	37	W
Operating and Storage Temperature Range		T_J, T_{stg}	-55 to 150	$^{\circ}\text{C}$
Junction-to-Ambient	$t \leq 10$	$R_{\theta JA}$	42	$^{\circ}\text{C/W}$
Junction-to-Ambient	Steady-State		78	
Junction-to-Case	Steady-State	$R_{\theta JC}$	3.4	

电性能参数 / Electrical Characteristics(Ta=25°C)

参数 Parameter	符号 Symbol	测试条件 Test Conditions	最小值 Min	典型值 Typ	最大值 Max	单位 Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V$ $I_D=250\mu A$	40	47		V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=40V$ $V_{GS}=0V$			1	μA
Gate-Body Leakage Current Forward	I_{GSS}	$V_{GS}=\pm 20V$ $V_{DS}=0V$			± 0.1	μA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ $I_D=250\mu A$	1.0	1.7	3.0	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=10V$ $I_D=20A$		2.5	3	m Ω
		$V_{GS}=4.5V$ $I_D=10A$		3.5	5	m Ω
Drain-Source Diode Forward Voltage	V_{SD}	$V_{GS}=0V$ $I_S=1A$			1.2	V
Input Capacitance	C_{iss}	$V_{DS}=25V$ $V_{GS}=0V$ $f=1.0MHz$		9600		pF
Output Capacitance	C_{oss}			740		
Reverse Transfer Capacitance	C_{rss}			650		
Gate resistance	R_g	$V_{GS}=0V$ $V_{DS}=0V$ $f=1MHz$		1.3		Ω
Total Gate Charge	$Q_{g(10V)}$	$V_{GS}=10V$ $V_{DS}=20V$ $I_D=20A$		51		nC
Total Gate Charge	$Q_{g(4.5V)}$			23		
Gate Source Charge	Q_{gs}			13.2		
Gate Drain Charge	Q_{gd}			3.1		
Turn-On Delay Time	$t_{d(on)}$	$V_{GS}=10V$ $V_{DS}=20V$ $R_L=1\Omega$ $R_{GEN}=3.0\Omega$		11		ns
Turn-On Rise Time	t_r			11		
Turn-Off Delay Time	$t_{d(off)}$			40		
Turn-Off Fall Time	t_f			10		

电参数曲线图 / Electrical Characteristic Curve

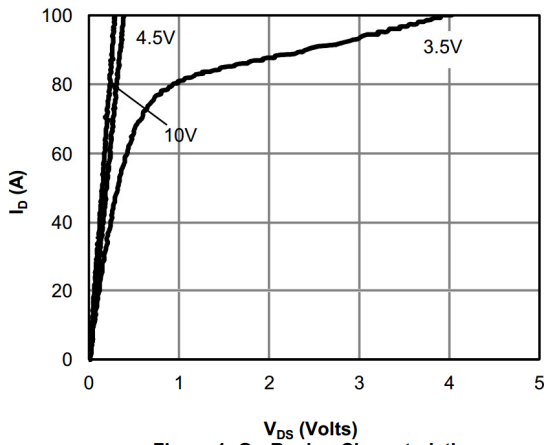


Figure 1: On-Region Characteristics

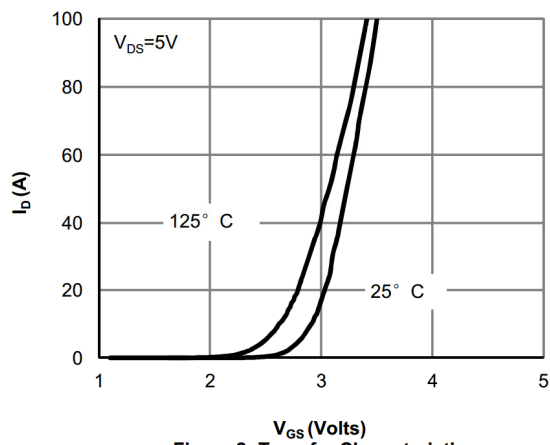


Figure 2: Transfer Characteristics

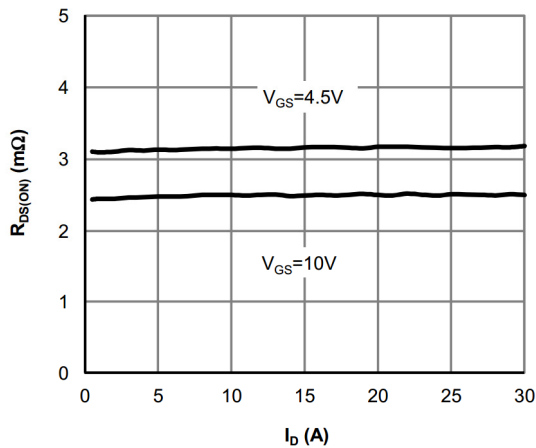


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

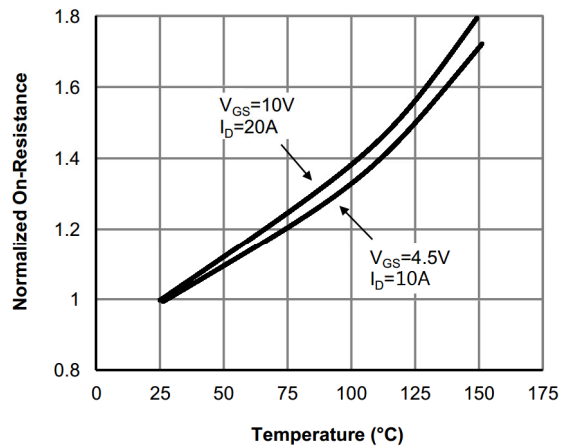


Figure 4: On-Resistance vs. Junction Temperature

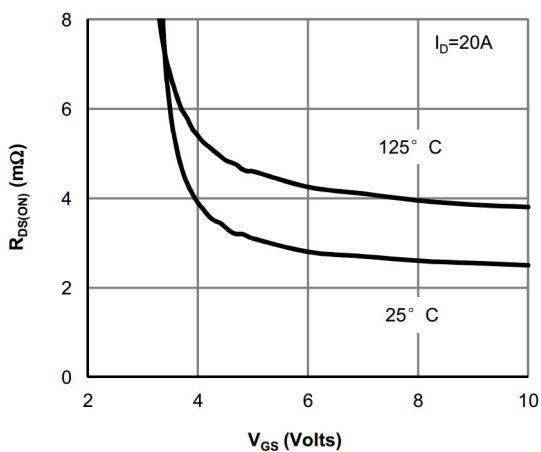


Figure 5: On-Resistance vs. Gate-Source Voltage

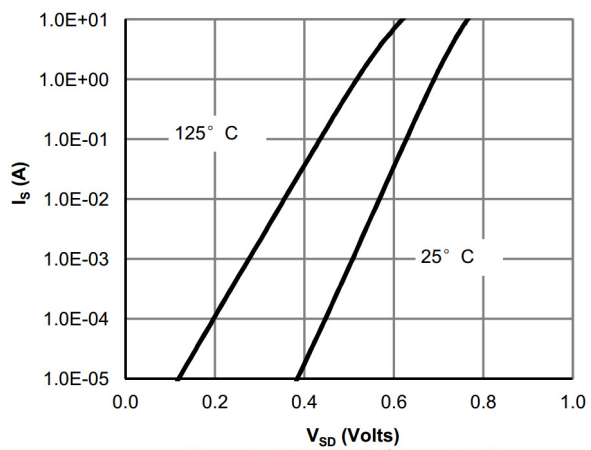
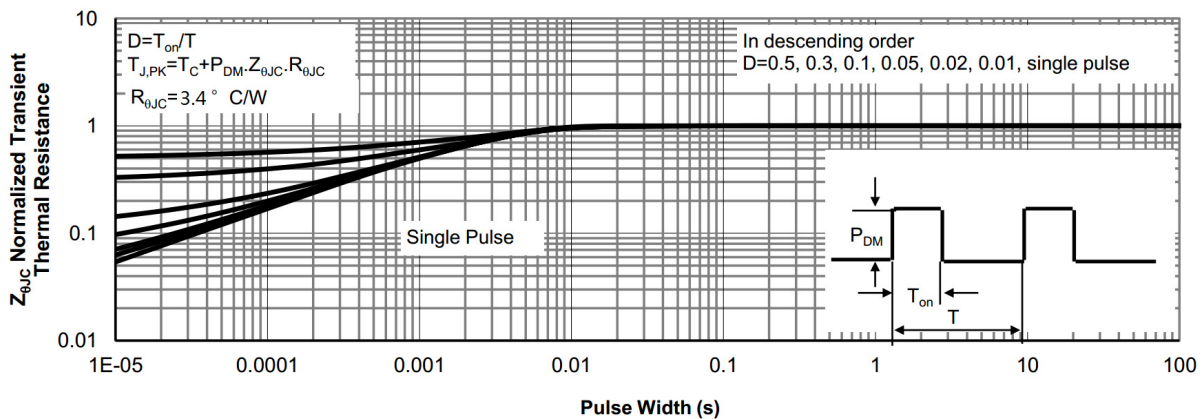
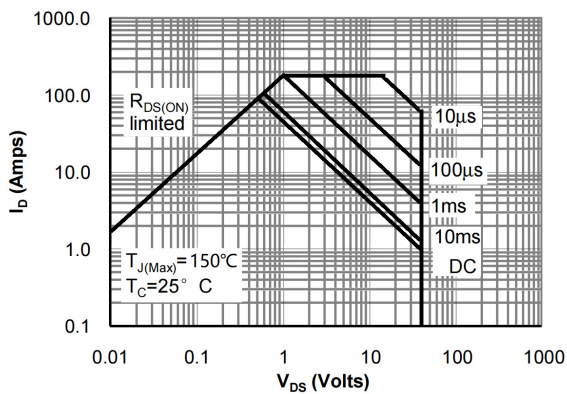
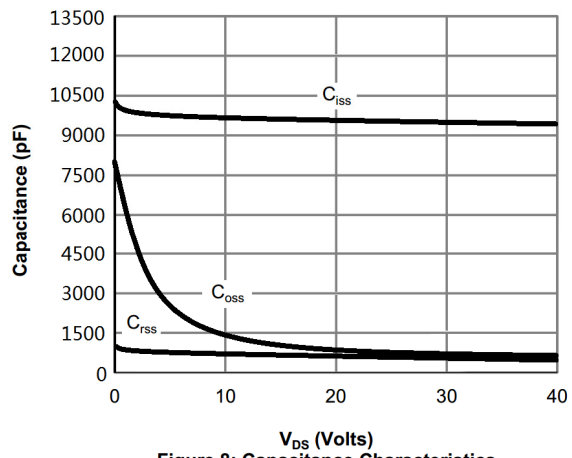
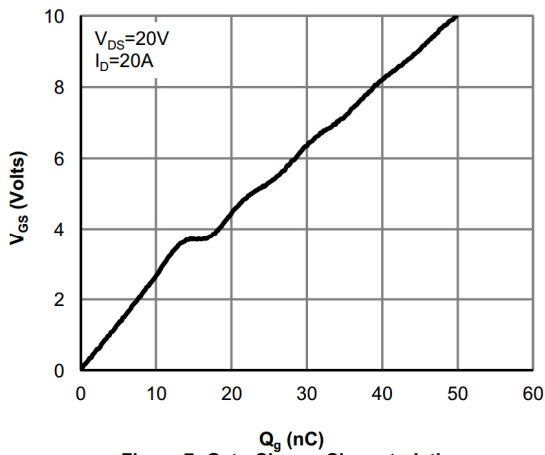


Figure 6: Body-Diode Characteristics

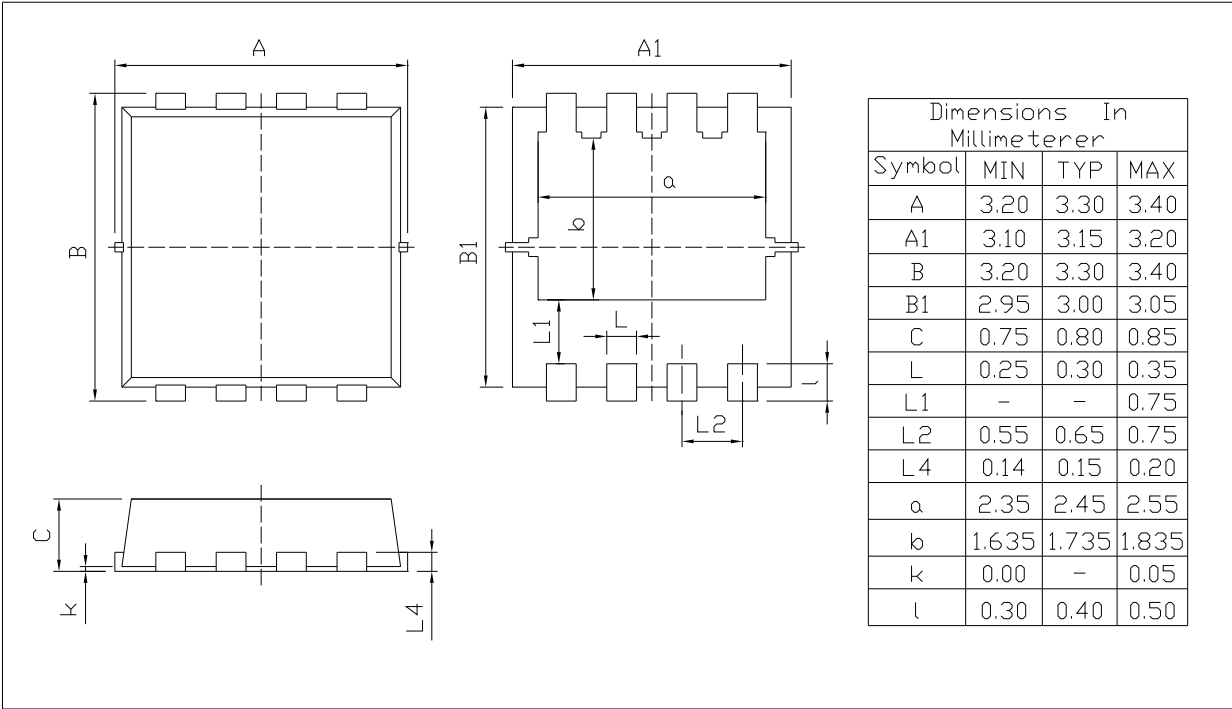
电参数曲线图 / Electrical Characteristic Curve



外形尺寸图 / Package Dimensions

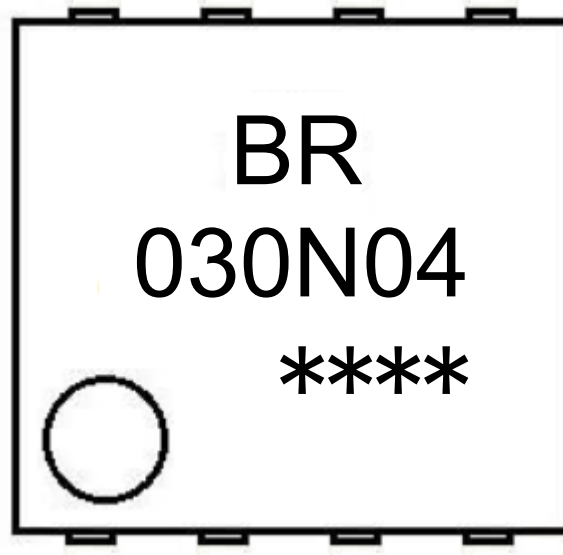
PDFN3X3A-8L

Unit:mm



Rev.00 202011

印章说明 / Marking Instructions



说明：

BR： 为公司代码

030N04： 为型号代码

****： 为生产批号代码，随生产批号变化

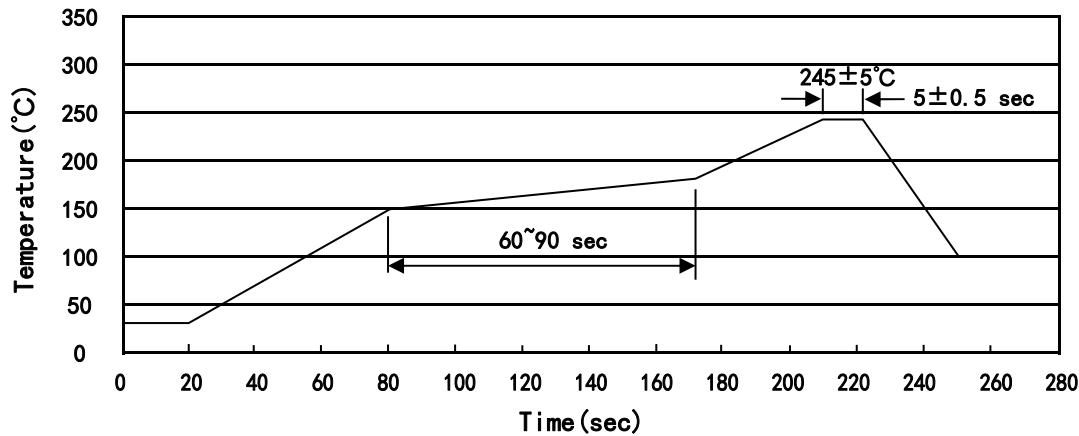
Note:

BR: Company Code

030N04: Product Type Code

****: Lot No. Code, code change with Lot No

回流焊温度曲线图(无铅) / Temperature Profile for IR Reflow Soldering(Pb-Free)



说明：

- 1、预热温度 150~180°C，时间 60~90sec;
- 2、峰值温度 245±5°C，时间持续为 5±0.5sec;
- 3、焊接制程冷却速度为 2~10°C/sec.

Note:

- 1.Preheating:150~180°C, Time:60~90sec.
- 2.Peak Temp.:245±5°C, Duration:5±0.5sec.
3. Cooling Speed: 2~10°C/sec.

耐焊接热试验条件 / Resistance to Soldering Heat Test Conditions

温度：260±5°C

时间：10±1 sec.

Temp.:260±5°C

Time:10±1 sec

包装规格 / Packaging SPEC.

卷盘包装 / REEL

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm ³)		
	Units/Reel 只/卷盘	Reels/Inner Box 卷盘/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Reel	Inner Box 盒	Outer Box 箱
PDFN3×3A-8L	5,000	2	10,000	6	60,000	13" ×12	360×360×50	380×335×366

使用说明 / Notices